

GSM2308A

60V N-Channel Enhancement Mode MOSFET

Product Description

GSM2308A, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

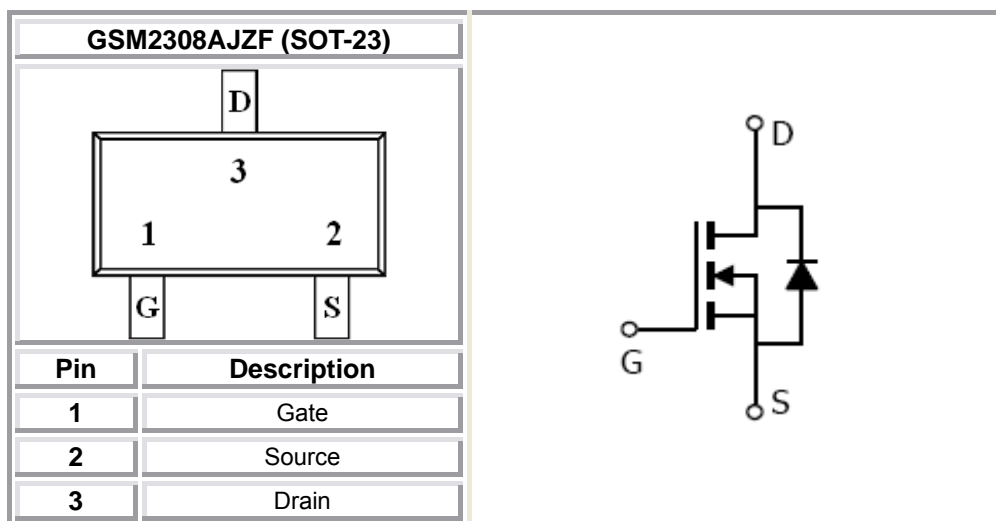
Features

- 60V/2.8A, $R_{DS(ON)}=135m\Omega@V_{GS}=10V$
- 60V/2.0A, $R_{DS(ON)}=145m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

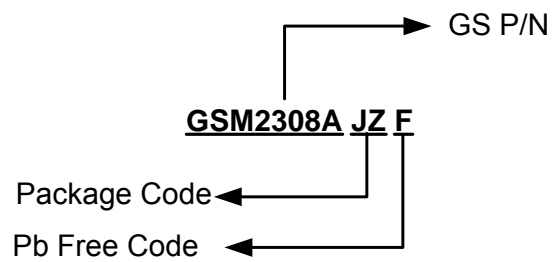
Applications

- Portable Equipment
- Battery Powered System
- Net Working System

Packages & Pin Assignments

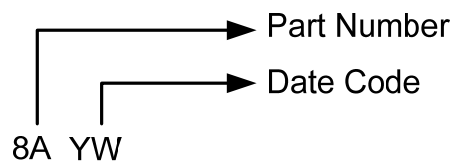


Ordering Information



Part Number	Package	Quantity Reel
GSM2308AJZF	SOT-23	3000 PCS

Marking Information



Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

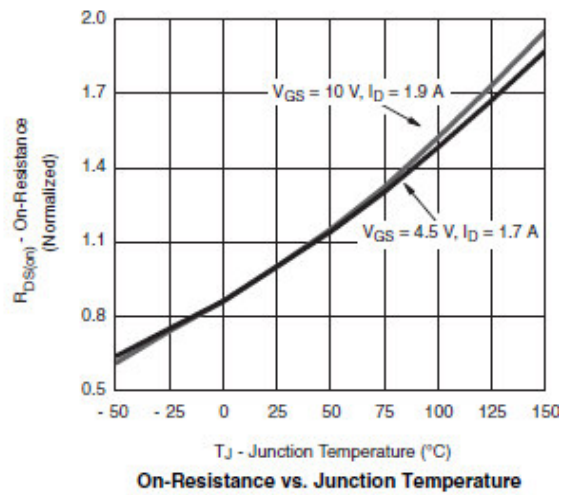
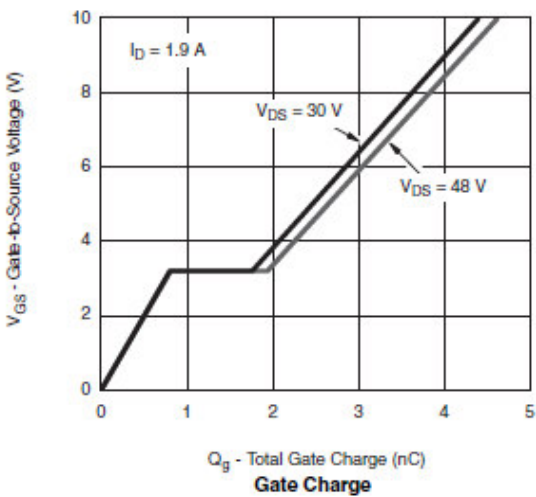
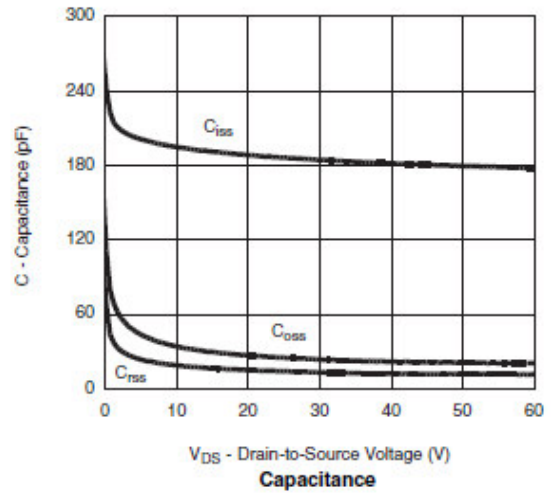
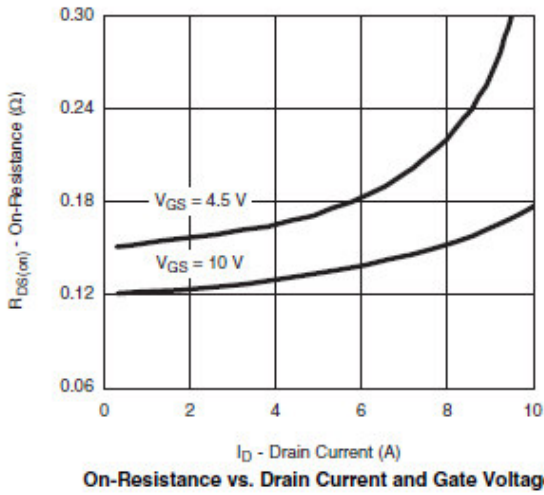
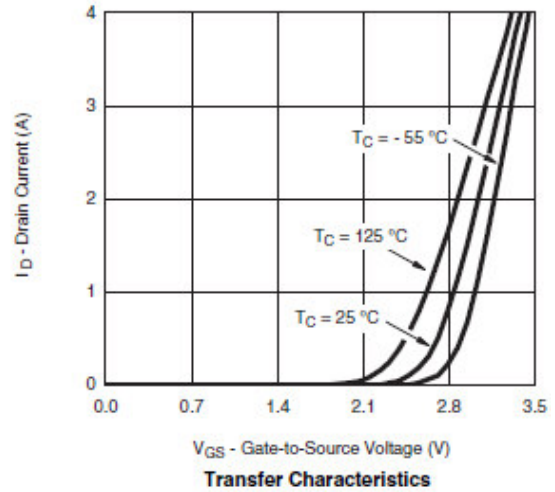
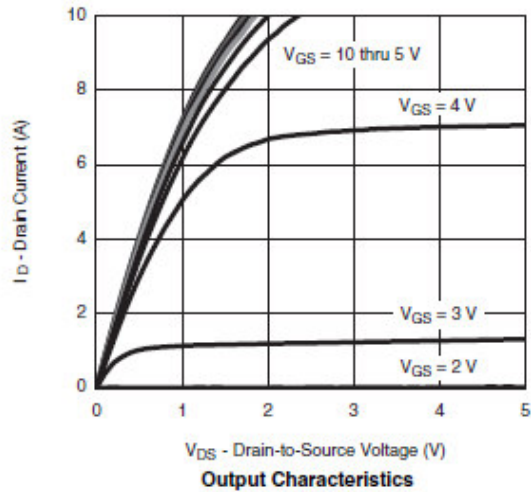
Symbol	Parameter	Typical	Unit
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate -Source Voltage	±20	V
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	2.8
		T _A =70°C	2.0
I _{DM}	Pulsed Drain Current	8	A
I _S	Continuous Source Current(Diode Conduction)	1.2	A
P _D	Power Dissipation	T _A =25°C	1.25
		T _A =70°C	0.8
T _J	Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55/150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	120	°C/W

Electrical Characteristics

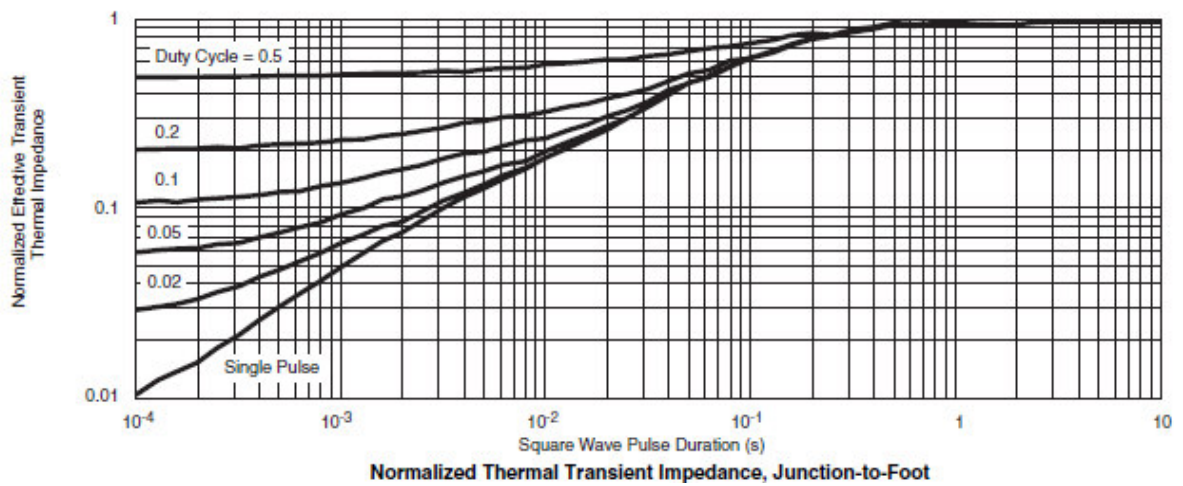
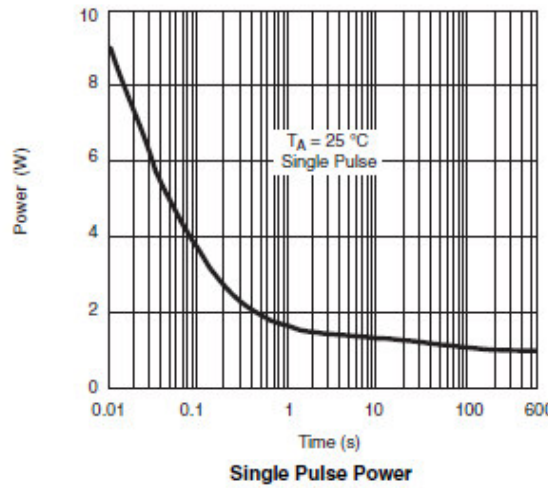
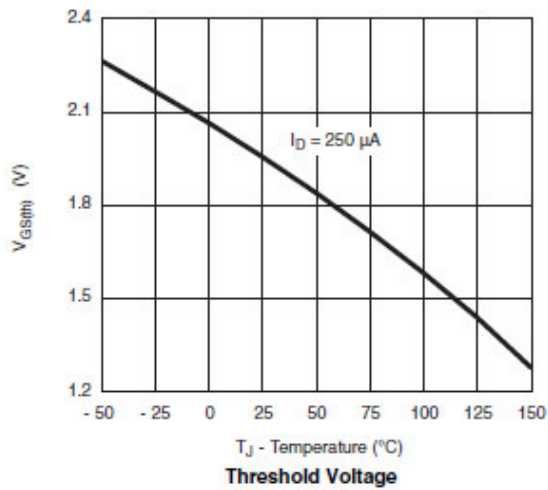
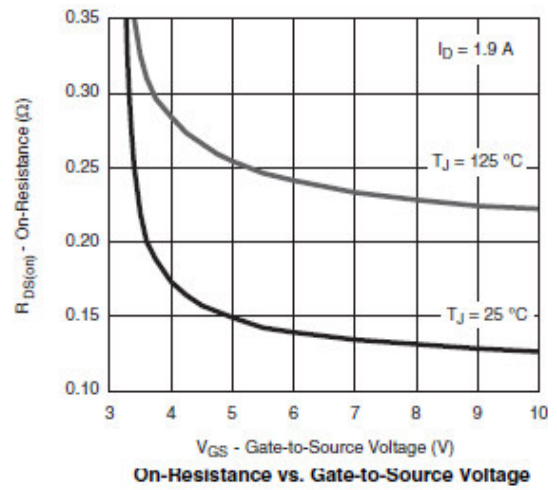
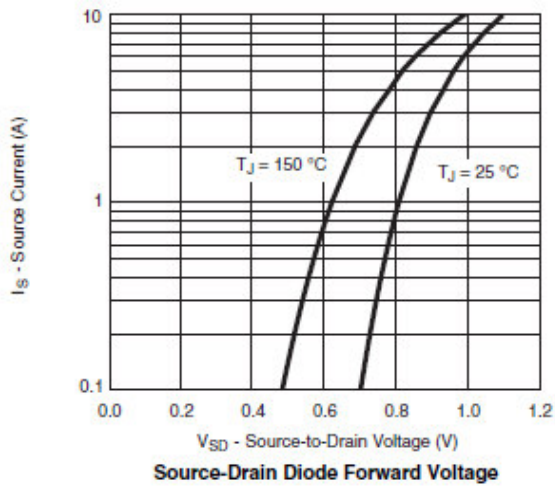
($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.7		2.5	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48V, V_{GS}=0V$			1	uA
		$V_{DS}=48V, V_{GS}=0V, T_J=85^\circ\text{C}$			10	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 5V, V_{GS}=10V$	5			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=2.8A$		110	135	m Ω
		$V_{GS}=4.5V, I_D=2.0A$		120	145	
g_{FS}	Forward Transconductance	$V_{DS}=15V, I_D=2.0A$		5		S
V_{SD}	Diode Forward Voltage	$I_S=2.5A, V_{GS}=0V$		0.85	1.2	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$		200		pF
C_{oss}	Output Capacitance			20		
C_{rss}	Reverse Transfer Capacitance			10		
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=4.5V, I_D=2.0A$		2.5	3.5	nC
Q_{gs}	Gate-Source Charge			0.8		
Q_{gd}	Gate-Drain Charge			1.0		
$t_{d(on)}$	Turn-On Time	$V_{DD}=30V, R_L=20\Omega, I_D=1.5A, V_{GEN}=10V, R_G=1\Omega$		4	8	ns
t_r				10	20	
$t_{d(off)}$	Turn-Off Time			10	40	
t_f				6	10	

Typical Performance Characteristics

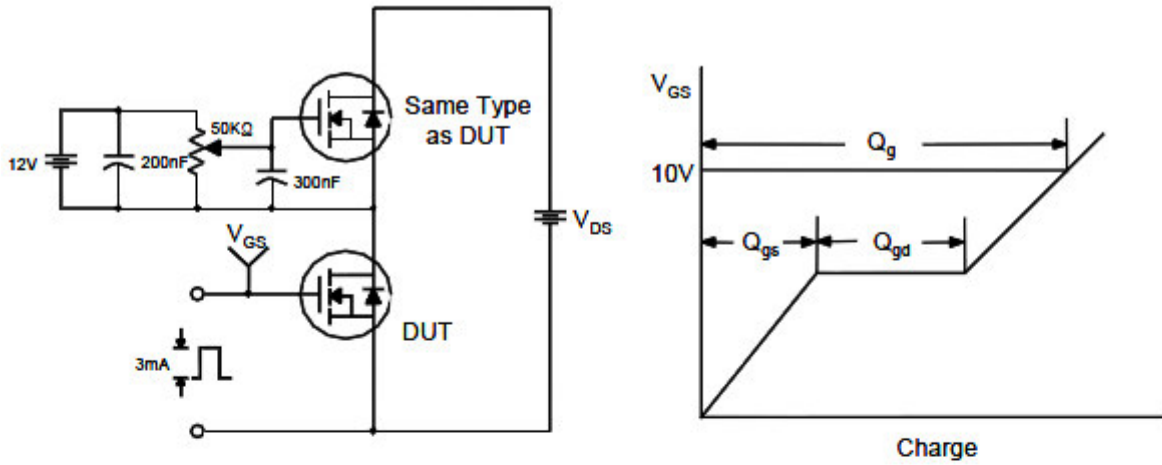


Typical Performance Characteristics (continue)

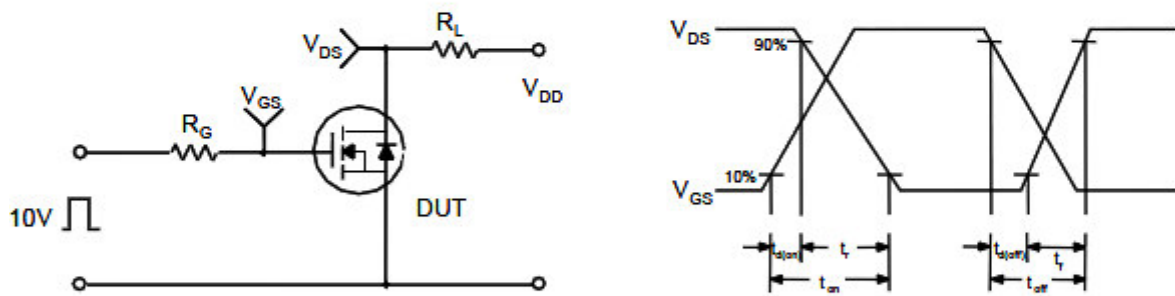


Typical Performance Characteristics (continue)

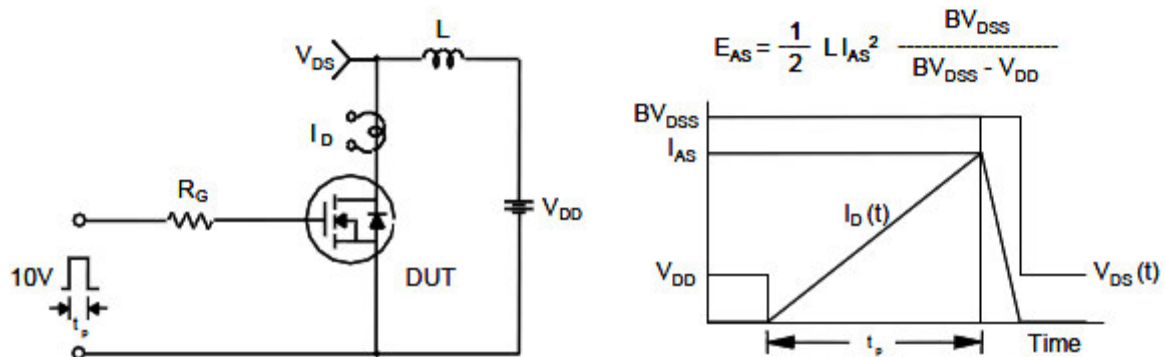
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

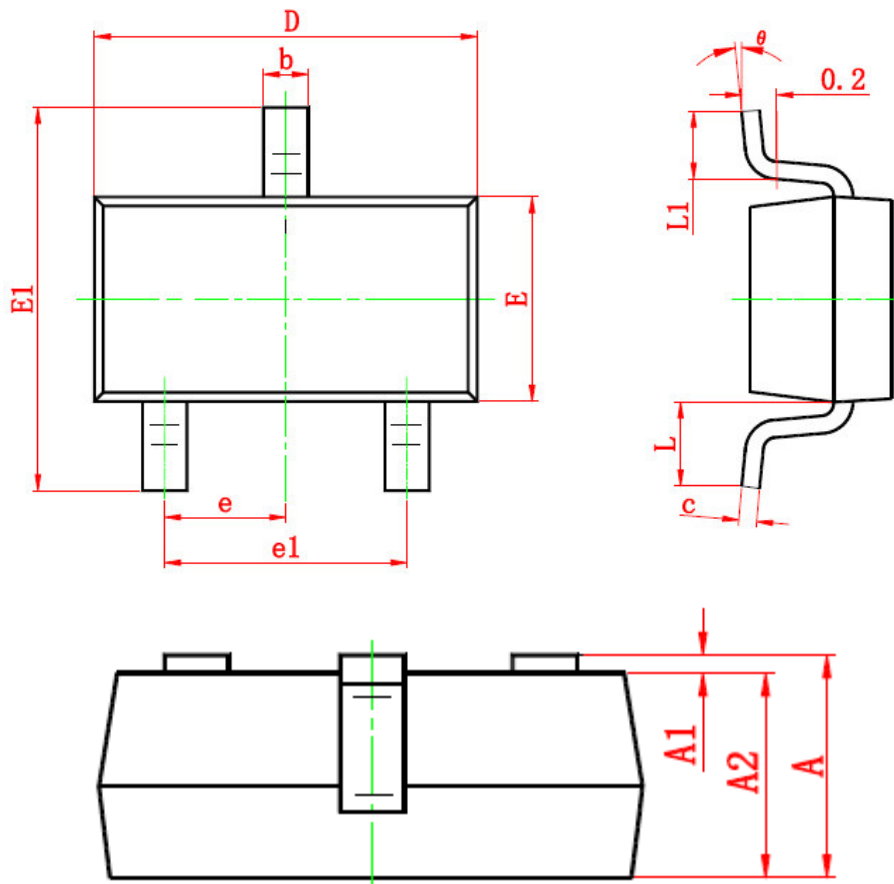


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOT-23 PLASTIC PACKAGE







Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.90	1.20	0.035	0.043
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.039
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950 (TYP)		0.037 (TYP)	
e1	1.80	2.00	0.071	0.079
L	0.550 (REF)		0.022 (REF)	
L1	0.30	0.50	0.012	0.020
Q	0°	8°	0°	8°



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